

High-Voltage Rectifier Diodes

Parameter Type No.	Absolute Maximum Ratings					Electrical Characteristics (Ta=25°C)							Others																																																						
	V _{RM} (kV)	I _{F(AV)} (mA)	I _{FSM} (A) 50Hz Half-cycle Sinewave Single Shot	T _c (°C)	T _{stg} (°C)	V _F (V)		I _R (μA) V _R =V _{RM} max	I _{R(H)} (μA) V _R =V _{RM} Ta=100°C max	t _{rr} (μs)			Mass (g)	Fig.	Remarks																																																				
						max	I _F (mA)			I _F /I _{RP} (mA)	Ta=100°C																																																								
SHV-02	2	2.0 TV high voltage rectifier Capacitive load	0.3	100	-40 to +120	16	10	1	3	0.18	10/10	—	0.13	A	For general FBT																																																				
SHV-03S	3															0.5	100	-40 to +120	40	10	1	3	0.18	10/10	—	0.16	B	For general FBT																																							
SHV-03	3																												0.5	100	-40 to +120	45	10	1	3	0.18	10/10	—	0.33	E	For general FBT																										
SHV-10	10																																									0.5	100	-40 to +120	55	10	1	3	0.18	10/10	—	0.33	E	For general FBT													
SHV-12	12																																																						0.5	100	-40 to +120	60	10	1	3	0.18	10/10	—	0.33	E	For general FBT
SHV-14	14																																																																		
SHV-16	16															2.0 TV high voltage rectifier Capacitive load	0.5	100	-40 to +120	24	10	1	3	0.15	10/10	0.20	0.17	C	For high- frequency layer-built FBT																																						
SHV-20	20																													0.5	100	-40 to +120	30	10	1	3	0.15	10/10	0.20	0.20	D	For high- frequency layer-built FBT																									
SHV-24	24																																										0.5	100	-40 to +120	38	10	1	3	0.15	10/10	0.20	0.20	D	For high- frequency layer-built FBT												
SHV-06EN	6																																																							0.5	100	-40 to +120	45	10	1	3	0.15	10/10	0.20	0.20	D
SHV-08EN	8	0.5	100	-40 to +120	30	10	1	3	0.15	10/10	0.20	0.17	C	For Ultra high-frequency layer-built FBT																																																					
SHV-10EN	10														0.5															100	-40 to +120	38	10	1	3	0.15	10/10	0.20	0.20	D	For Ultra high-frequency layer-built FBT																										
SHV-08DN	8	0.5	100	-40 to +120	30	10	1	3	0.15	10/10	0.20	0.17	C	For Ultra high-frequency layer-built FBT																																																					
SHV-10DN	10														0.5															100	-40 to +120	38	10	1	3	0.15	10/10	0.20	0.20	D	For Ultra high-frequency layer-built FBT																										
SHV-12DN	12	0.5	100	-40 to +120	45	10	1	3	0.15	10/10	0.20	0.20	D	For Ultra high-frequency layer-built FBT																																																					
HVR-1X-40B	9														350															20	60 (Ta)	-40 to +130	9	350	10	V _Z =9.5 to 15kV	—	—	2.5	G	For Microwave Oven																										
UX-F0B	8	15	-30 to +130	16	V _Z =8.5kV min.	0.18	100/100	2.5	H	For Inverter-type Microwave Oven																																																									

Type No.	External Dimensions (Unit: mm)	Marking (Cathode Mark)	
		Pattern	Color
SHV-02	Fig. A 		White
SHV-03S			Red
SHV-03	Fig. B 		White
SHV-06EN	Fig. C 		White
SHV-08EN			White
SHV-08DN			Red
SHV-10EN	Fig. D 		White
SHV-10DN			Red
SHV-12EN			White
SHV-12DN			Red

Type No.	External Dimensions (Unit: mm)	Marking (Cathode Mark)	
		Pattern	Color
SHV-10	Fig. ㉔ 		White
SHV-12			
SHV-14			
SHV-16	Fig. ㉕ 		White
SHV-20			
SHV-24			

- The SHV series of diodes have been miniaturized by resin on the assumption for remolding. Measures against creeping discharge and humidity stress must be taken when using these diodes.
- The taping specifications of the SHV series differ from ordinary diodes. (P.10)

SHV series

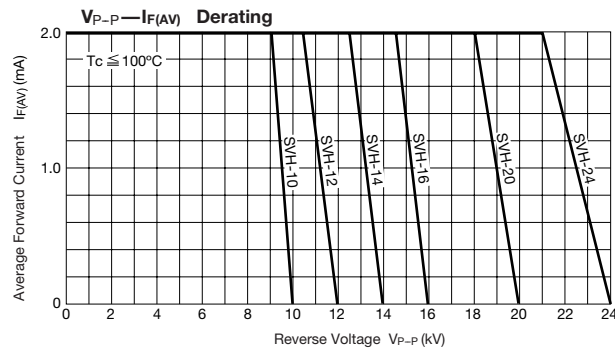


Fig. ㉔

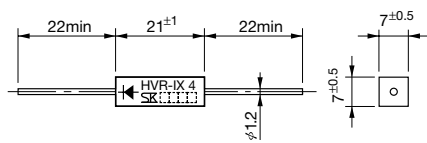


Fig. ㉕

